

a gate insulating film comprising a first insulating film over the crystalline semiconductor island and a second insulating film over the first insulating film; and

a gate electrode over the gate insulating film, wherein the first insulating film has a side aligned with a side of the crystalline semiconductor island.

46. A semiconductor device comprising:

a crystalline semiconductor island comprising silicon over

E' a substrate, the crystalline semiconductor island comprising a source region, a drain region and a channel formation region provided between the source and the drain region; and

a gate insulating film comprising a first insulating film comprising silicon oxide cover the crystalline semiconductor island and a second insulating film comprising silicon oxide over the first insulating film; and

a gate electrode over the gate insulating film, wherein the first insulating film has a side aligned with a side of the crystalline semiconductor island.

47. A semiconductor device comprising:

a crystalline semiconductor island comprising silicon over

a substrate, the crystalline semiconductor island comprising a source region, a drain region and a channel formation region provided between the source and the drain region; and

a gate insulating film comprising a first insulating film comprising silicon oxide over the crystalline semiconductor

island and a second insulating film comprising silicon nitride over the first insulating film; and

a gate electrode over the gate insulating film,
wherein the first insulating film has a side aligned with a side of the crystalline semiconductor island.

48. A semiconductor device comprising:

a crystalline semiconductor island comprising silicon over

E' a substrate, the crystalline semiconductor island comprising a source region, a drain region and a channel formation region provided between the source and the drain region; and

a gate insulating film comprising a first insulating film comprising silicon nitride over the crystalline semiconductor island and a second insulating film comprising silicon oxide over the first insulating film; and

a gate electrode over the gate insulating film,
wherein the first insulating film has a side aligned with a side of the crystalline semiconductor island.

49. A semiconductor device comprising:

a crystalline semiconductor island comprising silicon over

a substrate, the crystalline semiconductor island comprising a source region, a drain region and a channel formation region provided between the source and the drain region; and

a gate insulating film comprising a first insulating film comprising silicon nitride over the crystalline

semiconductor island and a second insulating film comprising silicon nitride over the first insulating film; and
a gate electrode over the gate insulating film,
wherein the first insulating film has a side aligned with a side of the crystalline semiconductor island.

50. A semiconductor device according to claim 45, wherein the crystalline semiconductor island is formed by irradiating a laser light through the first insulating film.

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51. A semiconductor device according to claim 46, wherein the crystalline semiconductor island is formed by irradiating a laser light through the first insulating film.

52. A semiconductor device according to claim 47, wherein the crystalline semiconductor island is formed by irradiating a laser light through the first insulating film.

53. A semiconductor device according to claim 48, wherein the crystalline semiconductor island is formed by irradiating a laser light through the first insulating film.

54. A semiconductor device according to claim 49, wherein the crystalline semiconductor island is formed by irradiating a laser light through the first insulating film.

55. A semiconductor device according to claim 50, wherein the laser light is KrF excimer laser light or XeCl excimer laser light.

56. A semiconductor device according to claim 51, wherein the laser light is KrF excimer laser light or XeCl excimer laser light.

57. A semiconductor device according to claim 52, wherein the laser light is KrF excimer laser light or XeCl excimer laser light.

58. A semiconductor device according to claim 53, wherein the laser light is KrF excimer laser light or XeCl excimer laser light.

E1 59. A semiconductor device according to claim 54, wherein the laser light is KrF excimer laser light or XeCl excimer laser light.

60. A semiconductor device according to claim 45, wherein the substrate is a glass substrate.

61. A semiconductor device according to claim 46, wherein the substrate is a glass substrate.

62. A semiconductor device according to claim 47, wherein the substrate is a glass substrate.

63. A semiconductor device according to claim 48, wherein the substrate is a glass substrate.

64. A semiconductor device according to claim 49, wherein the substrate is a glass substrate.--